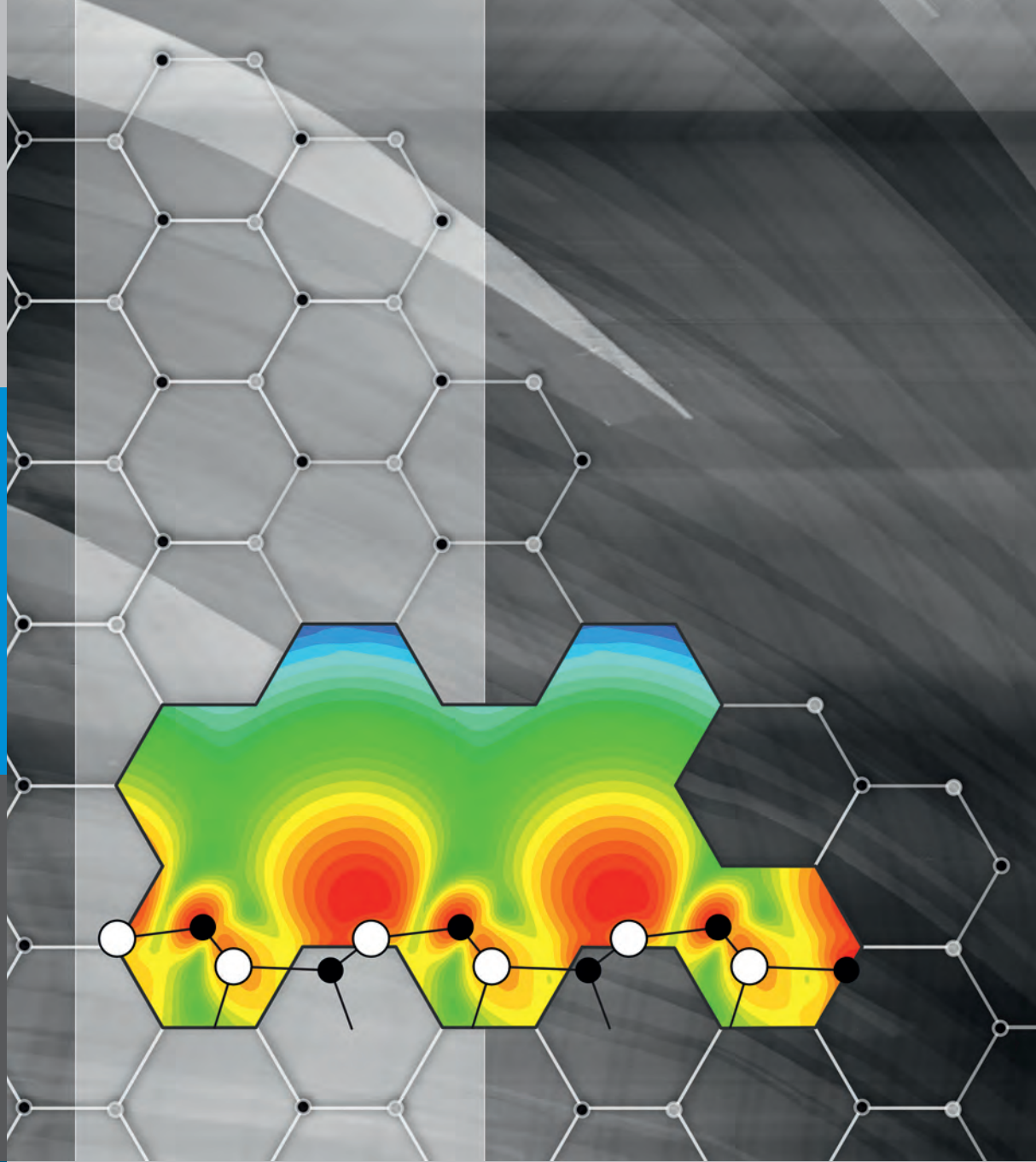




Structure, electronic properties, and interactions of defects in epitaxial GaN layers

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